


## Biodata

Name	Dr. V. N. Mani	
Designation	Scientist F ; Head, High Purity Materials Division	
Educational qualification	M.Sc. from University of Madras, Chennai. Ph.D. from Anna University, Chennai	
Research area	Purification of gallium, germanium, indium/packaging; processing/crystal growth of GaAs, GaSb, GaN and their characterization; epitaxial growth modeling; deposition of SiC/ZnO films; design and development of directional solidification/gradient process systems for purification of gallium/indium and recycling and recovery of high pure Ga,In, Si, Ge from spent GaAs, GaSb, InSb, Si and Ge electronic material(s) waste(s)	
Recognised Awards/Honors/Fellow	Nil	
Projects	Nil- planned to submit a new proposal on recycling and recovery of silicon from spent silicon waste to DST  Completed: Design and development of crystal growth system for preparation of high pure gallium nitride for light emitting diode (led) and other related optoelectronic applications-PI-(HD/SP/30) (Sponsored by DST, Outlay: Rs. 72.696 lakhs DoS: 04.09.2014; DoC: 31.03.2020) a) Total cost of C-MET, Hyderabad part of the Project: Rs.67.878 lakhs b) Total cost of Calcutta University part of the Project: Rs.4.818 lakhs	
Publications/Patents (Past 5 years)	1.Preparation of High Pure Crystalline Gallium Antimonide and its Characterization-V. N. Mani - Procs, Intl. Sym. on Semicond. Matls. & Devices, 02-05, Feb 2015, Anna University (p.166-169); 2.Directiona Freezing of Germanium - Some Select Results V. N. Mani - Procs. Intl. Sym. on Semicond. Matls. & Devices 02-05, Feb 2015 Anna University (p.192-195);	